

IN THE CLAIMS:

1. (Original) A method of growing a gallium nitride single crystal using a flux comprising at least sodium metal; said method comprising the step of:
growing said gallium nitride single crystal in an atmosphere comprising gas mixture comprising nitrogen gas under a total pressure of 300 atms or higher and 2000 atms or lower.
2. (Original) The method of claim 1, wherein said atmosphere has a nitrogen partial pressure of 100 atms or higher and 2000 atms or lower.
3. (Currently Amended) The method of ~~claims~~ claim 1 ~~or 2~~, wherein said crystal is grown at a temperature of 900°C or higher and 1500° or lower.
4. (Currently Amended) The method of ~~claims~~ claim 1 ~~or 2~~, wherein said crystal is grown at a temperature of 950°C or higher and 1200°C or lower.
5. (Currently Amended) The method of claim 1 ~~any one of claims 1 to 4~~, further comprising the step of elevating a crucible containing said flux so that a seed crystal contacts said flux.
6. (Currently Amended) The method of claim 1 ~~any one of claims 1 to 5~~, wherein said gallium nitride single crystal is grown using a system for hot isostatic press.
7. (Currently Amended) Gallium nitride single crystal grown by the method of claim 1 ~~any one of claims 1 to 6~~.